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View Online at https://aerobasegroup.com/nsn/5961-01-165-2735

Inclosure Material:

Metal

Overall Length:

Between 0.170 inches and 0.210 inches

Terminal Length:

Between 0.500 inches and 0.750 inches

Overall Diameter:

Between 0.209 inches and 0.230 inches

Internal Configuration:

Field effect

Joint Electronic Device Engineering Council/jedec/case Outline Designation:

To-18

Electrode Internally-electrically Connected To Case:

Gate

Mounting Method:

Terminal

Terminal Circle Diameter:

0.100 inches

Features Provided:

Burn in and quality assurance level txv

Semiconductor Material:

Silicon

Voltage Rating In Volts Per Characteristic:

-40.0 gate to source voltage and 40.0 drain to source voltage and 40.0 drain to gate voltage

Current Rating Per Characteristic:

50.00 milliamperes gate current

Power Rating Per Characteristic:

1.8 watts total power dissipation

Maximum Operating Tempurature Per Measurement Point:

200.0 degrees celsius junction

Precious Material And Location:

Terminal surfaces gold

Precious Material:

Gold

Test Data Document:

81349-mil-s-19500 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.).

Terminal Type And Quantity:

3 uninsulated wire lead

Specification Data:

81349-mil-s-19500/385 government specification

Shelf Life:

N/a

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Demilitarization:

No

Fiig:

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